

OptiMOS® 2 Power-Transistor

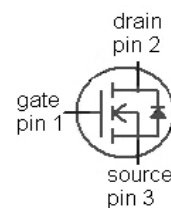
Features

- N-channel, normal level
- Excellent gate charge $\times R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target application
- Ideal for high-frequency switching and synchronous rectification

Product Summary

V_{DS}	85	V
$R_{DS(on),max}$	5.1	mΩ
I_D	100	A

Type	IPB051NE8N G	IPI054NE8N G	IPP054NE8N G
			
Package	PG-TO263-3	PG-TO262-3	PG-TO220-3
Marking	051NE8N	054NE8N	054NE8N



Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}^{2)}$	100	A
		$T_C=100\text{ °C}$	100	
Pulsed drain current ³⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	400	
Avalanche energy, single pulse	E_{AS}	$I_D=100\text{ A}$, $R_{GS}=25\text{ Ω}$	1000	mJ
Reverse diode dv/dt	dv/dt	$I_D=100\text{ A}$, $V_{DS}=80\text{ V}$, $di/dt=100\text{ A/μs}$, $T_{j,max}=175\text{ °C}$	6	kV/μs
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	300	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	0.5	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
junction - ambient		6 cm ² cooling area ⁴⁾	-	-	40	

Electrical characteristics, at $T_j=25\text{ }^{\circ}\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	85	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	2	3	4	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=85\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^{\circ}\text{C}$	-	0.01	1	μA
		$V_{DS}=85\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^{\circ}\text{C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=100\text{ A}$	-	4.1	5.4	m Ω
		$V_{GS}=10\text{ V}, I_D=100\text{ A},$ SMD version	-	3.8	5.1	
Gate resistance	R_G		-	1.8	-	Ω
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max},$ $I_D=100\text{ A}$	81	162	-	S

¹⁾J-STD20 and JESD22

²⁾ Current is limited by bondwire; with an $R_{thJC}=0.5\text{ K/W}$ the chip is able to carry 161 A.

³⁾ See figure 3

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	9220	12300	pF
Output capacitance	C_{oss}		-	2410	3210	
Reverse transfer capacitance	C_{rss}		-	210	315	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40\text{ V}, V_{GS}=10\text{ V},$ $I_D=50\text{ A}, R_G=1.6\ \Omega$	-	31	47	ns
Rise time	t_r		-	17	26	
Turn-off delay time	$t_{d(off)}$		-	58	87	
Fall time	t_f		-	15	22	

Gate Charge Characteristics⁵⁾

Gate to source charge	Q_{gs}	$V_{DD}=40\text{ V}, I_D=100\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	48	63	nC
Gate to drain charge	Q_{gd}		-	30	45	
Switching charge	Q_{sw}		-	63	89	
Gate charge total	Q_g		-	135	179	
Gate plateau voltage	$V_{plateau}$		-	5.2	-	V
Output charge	Q_{oss}	$V_{DD}=40\text{ V}, V_{GS}=0\text{ V}$	-	126	168	nC

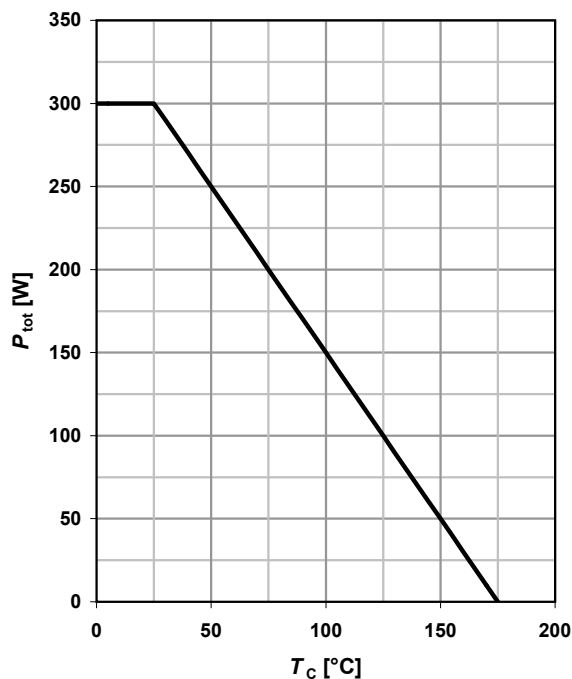
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ °C}$	-	-	100	A
Diode pulse current	$I_{S,pulse}$		-	-	400	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=100\text{ A},$ $T_j=25\text{ °C}$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=40\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	110		ns
Reverse recovery charge	Q_{rr}		-	360	-	nC

⁵⁾ See figure 16 for gate charge parameter definition

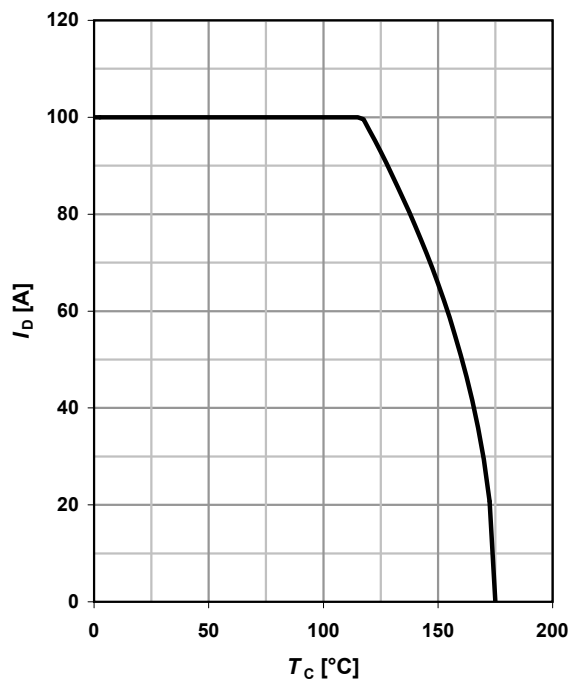
1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



2 Drain current

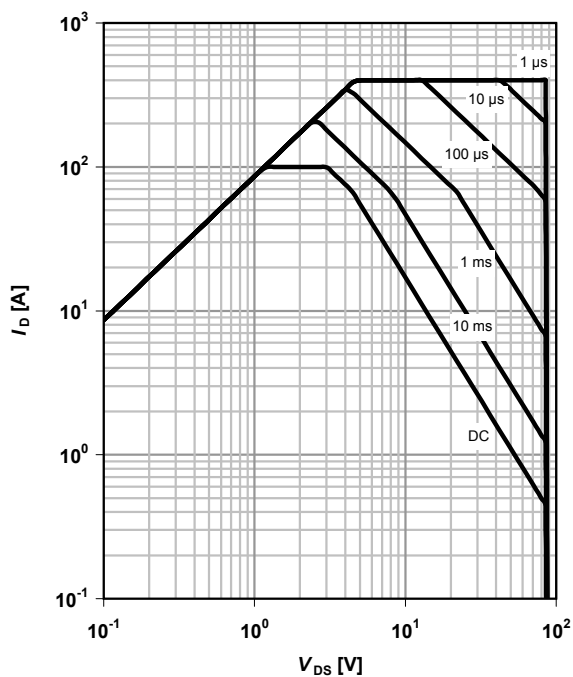
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

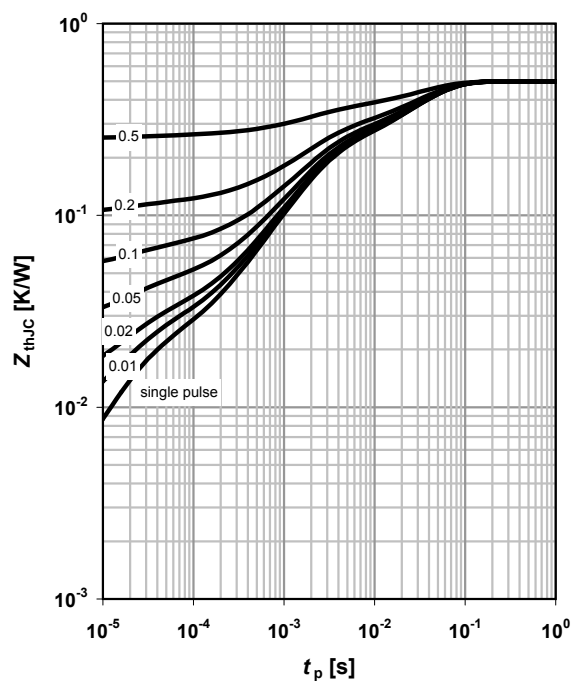
parameter: t_p



4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

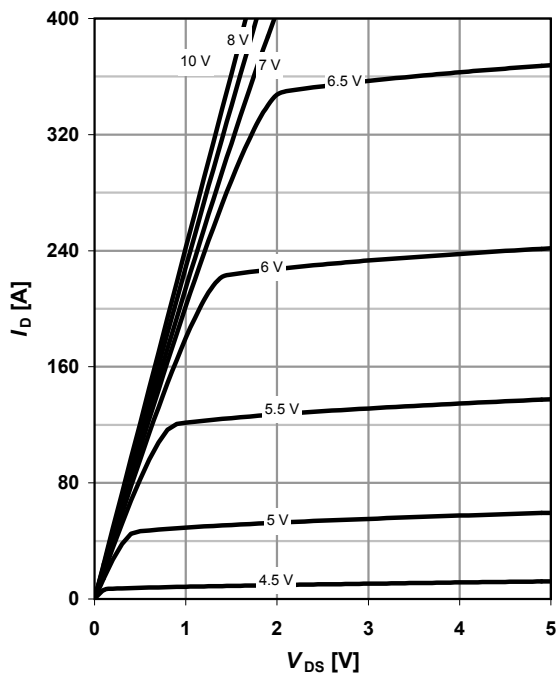
parameter: $D = t_p / T$



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

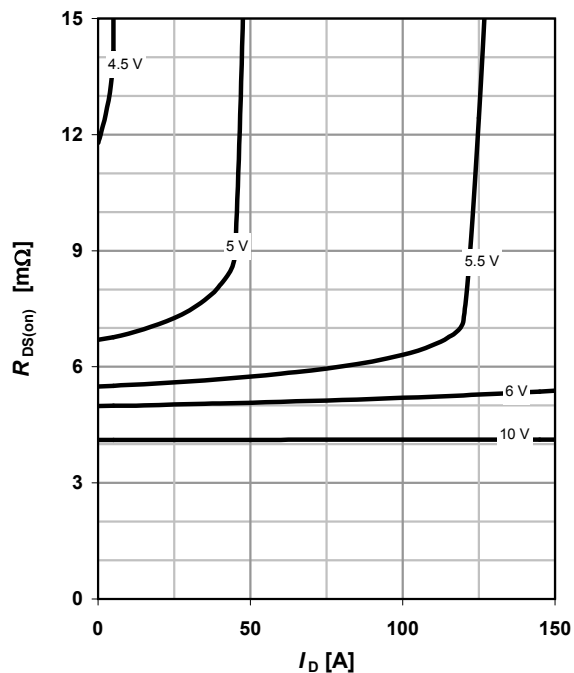
parameter: V_{GS}



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

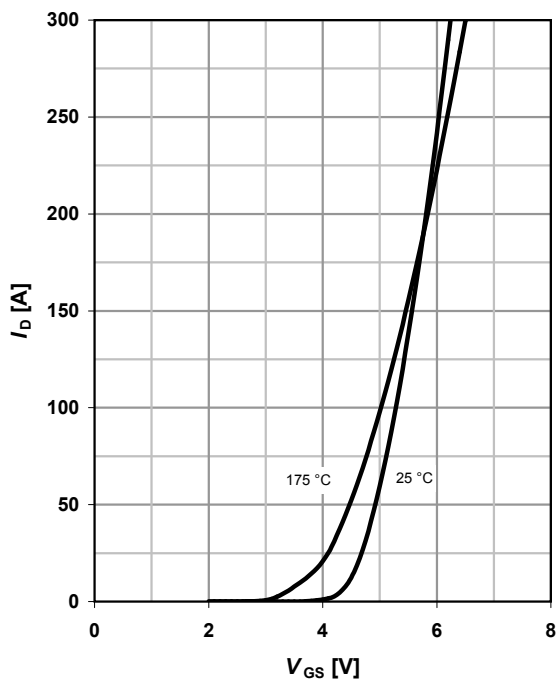
parameter: V_{GS}



7 Typ. transfer characteristics

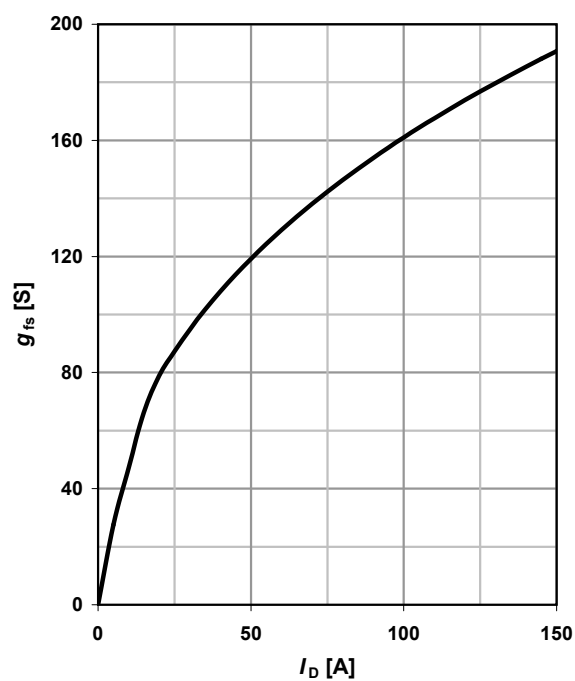
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter: T_j



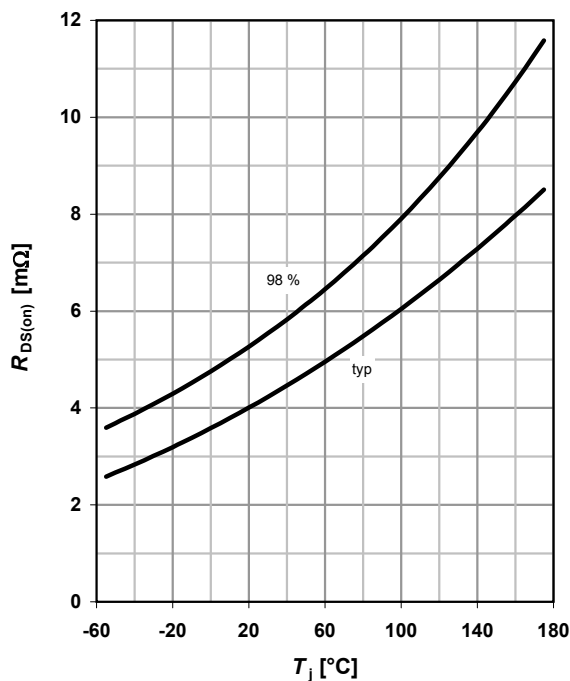
8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$



9 Drain-source on-state resistance

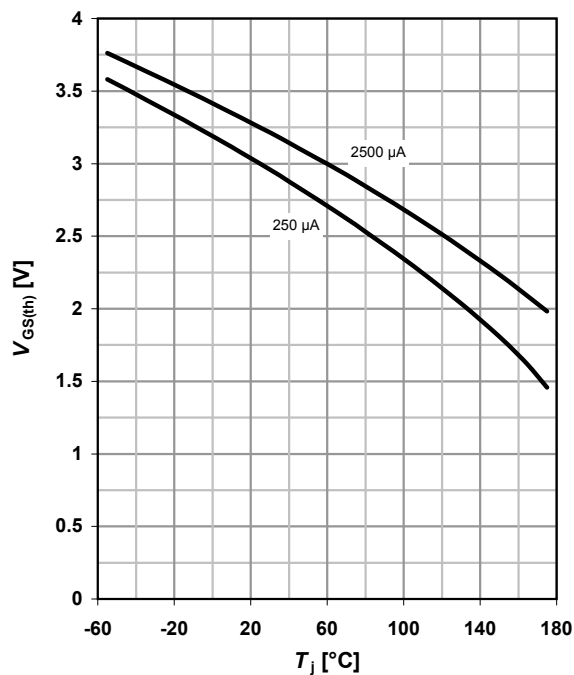
$$R_{DS(on)} = f(T_j); I_D = 100 \text{ A}; V_{GS} = 10 \text{ V}$$



10 Typ. gate threshold voltage

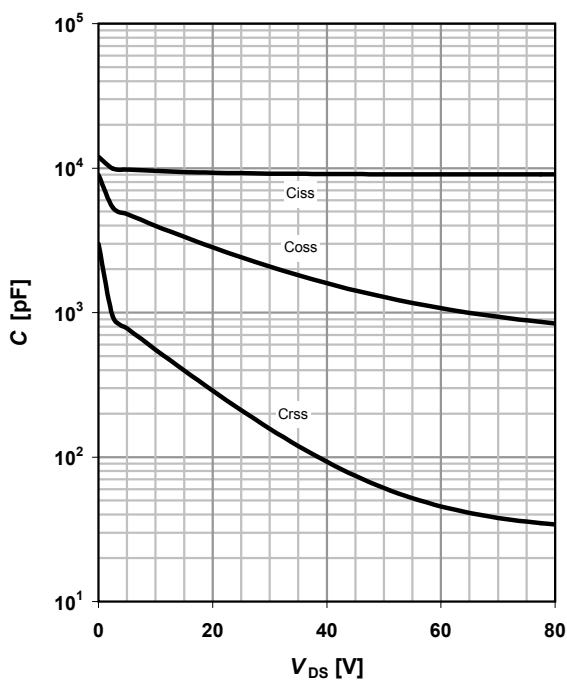
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



11 Typ. capacitances

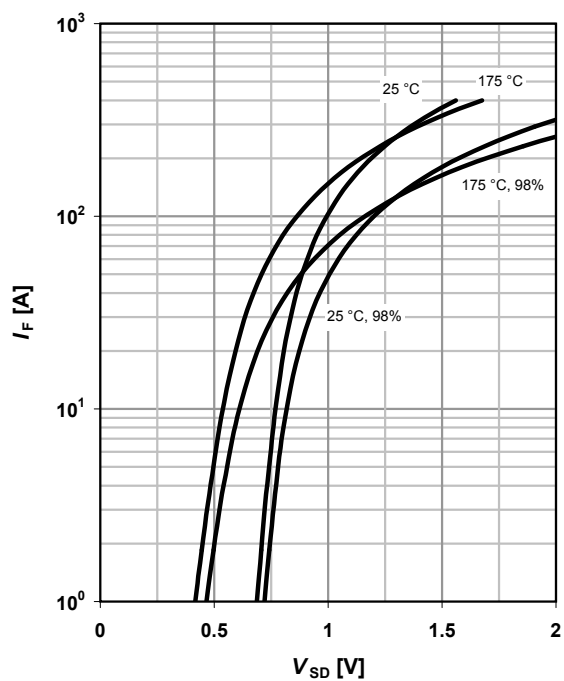
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

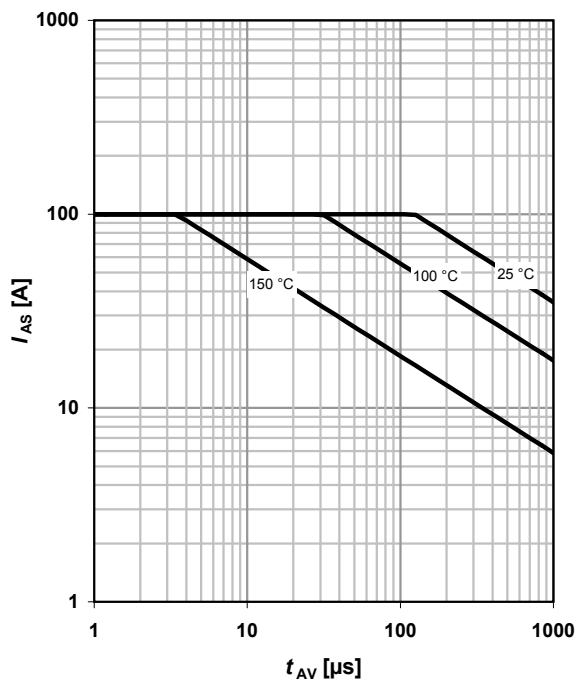
parameter: T_j



13 Avalanche characteristics

$$I_{AS} = f(t_{AV}); R_{GS} = 25 \, \Omega$$

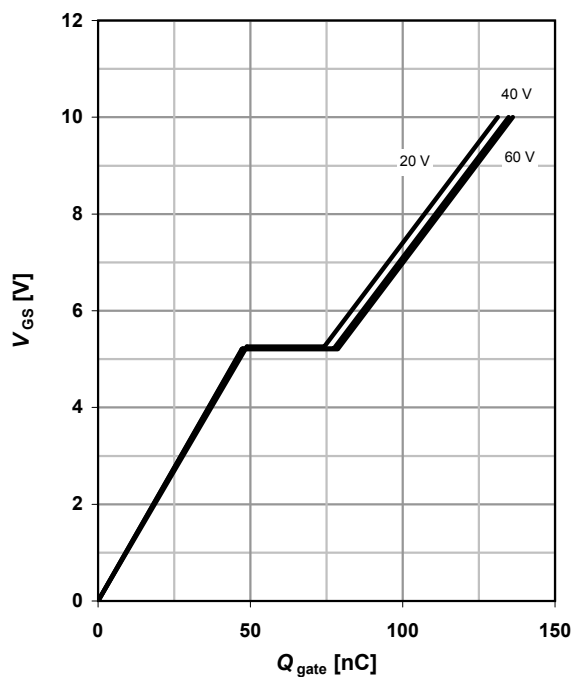
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

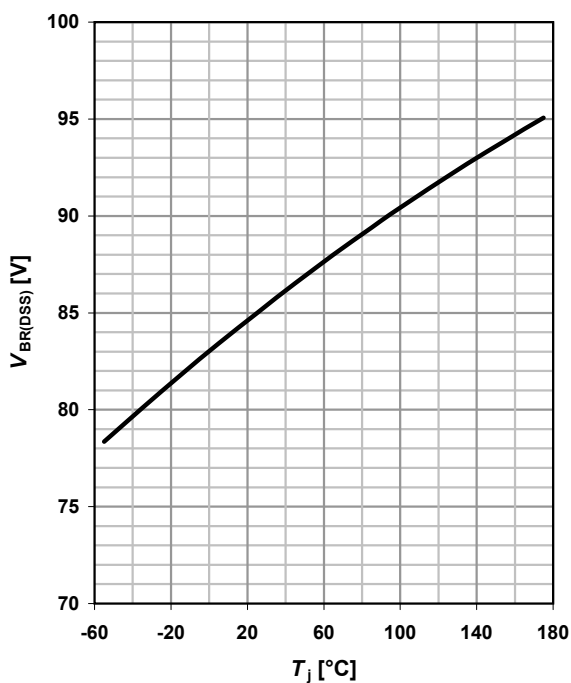
$$V_{GS} = f(Q_{\text{gate}}); I_D = 100 \, \text{A pulsed}$$

parameter: V_{DD}

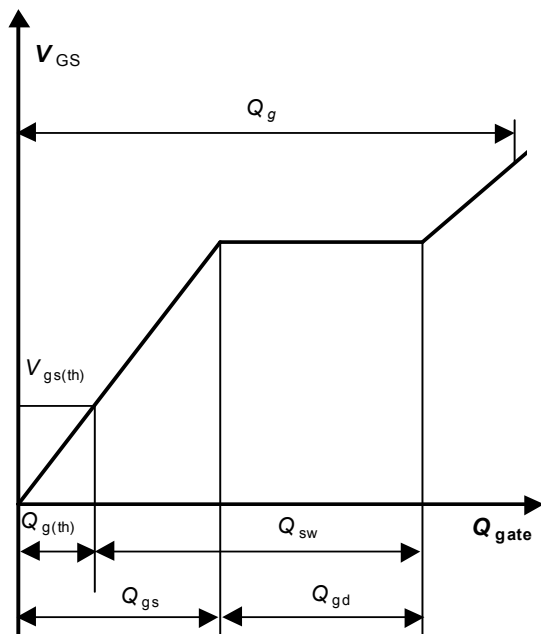


15 Drain-source breakdown voltage

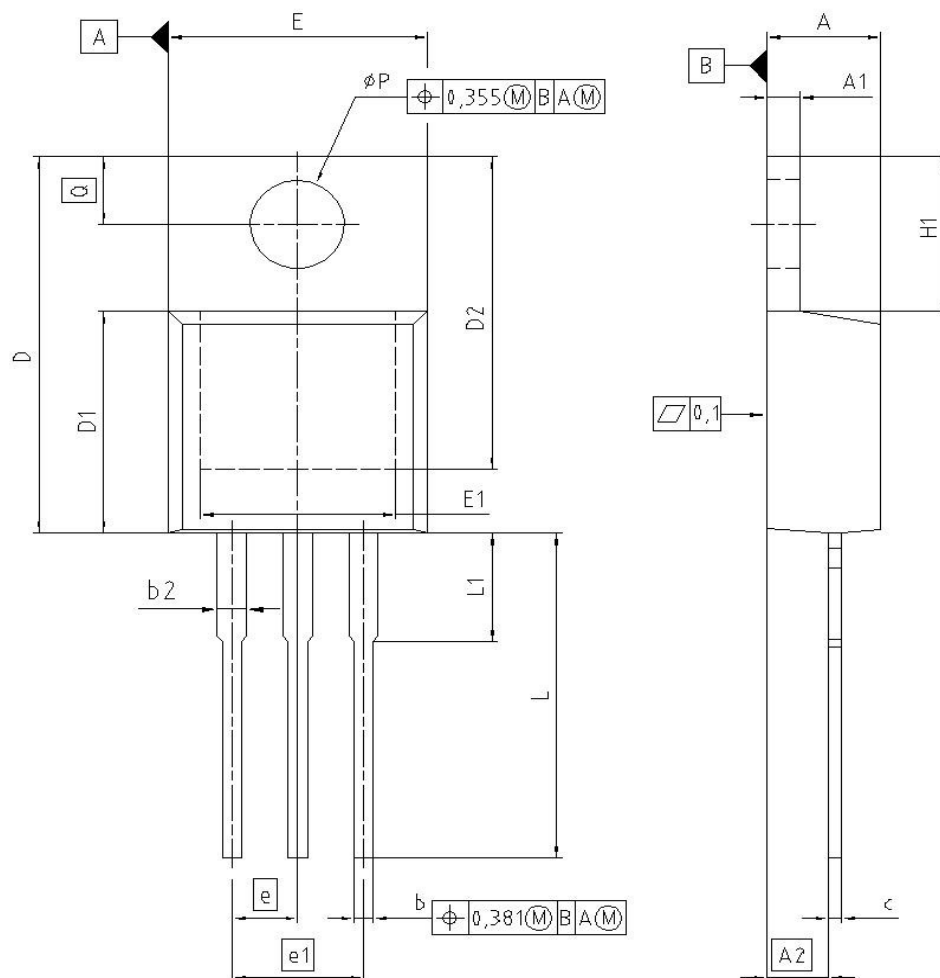
$$V_{BR(DSS)} = f(T_j); I_D = 1 \, \text{mA}$$



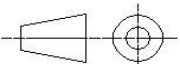
16 Gate charge waveforms



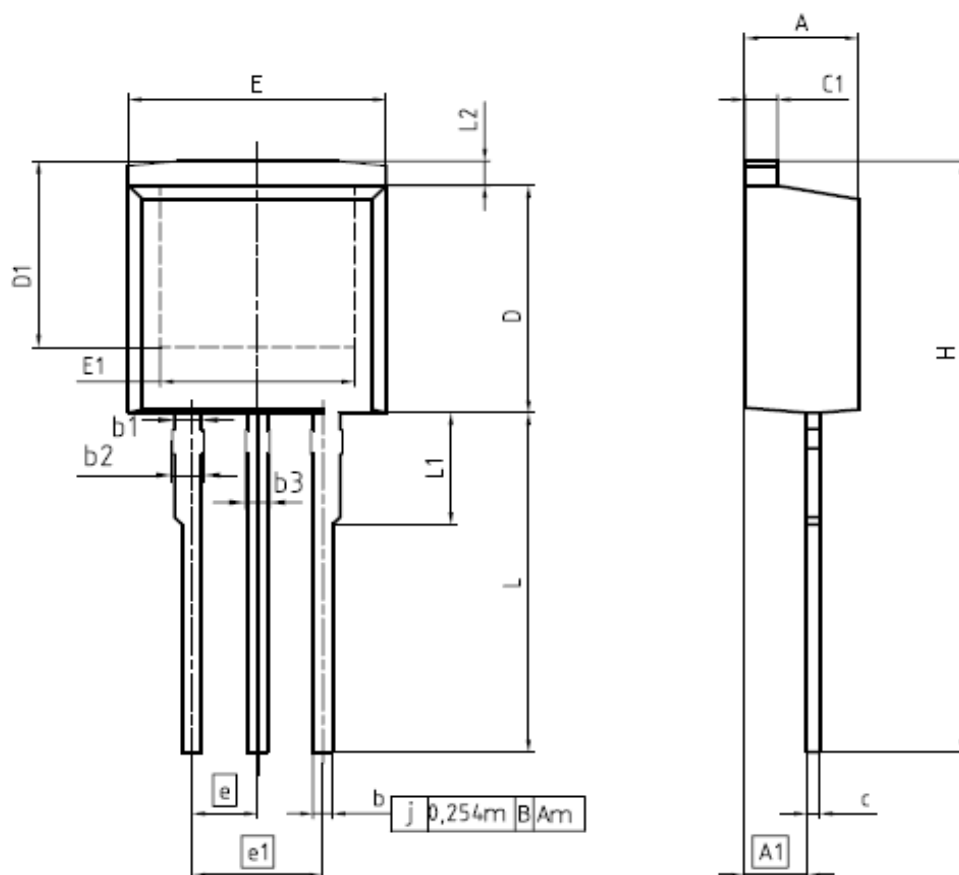
PG-TO220-3: Outline



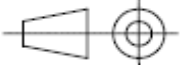
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	1.170	1.400	0.046	0.055
A2	2.215	2.718	0.087	0.107
b	0.650	0.864	0.026	0.034
b2	0.635	1.778	0.025	0.070
c	0.330	0.600	0.013	0.024
D	14.808	15.950	0.583	0.628
D1	8.509	9.450	0.335	0.372
D2	12.850	13.100	0.506	0.516
E	9.700	10.363	0.382	0.408
E1	6.500	8.600	0.256	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
H1	5.900	6.900	0.232	0.272
L	13.000	14.000	0.512	0.551
L1	-	4.800	-	0.189
Q	3.700	3.886	0.146	0.153
Q	2.600	3.000	0.102	0.118

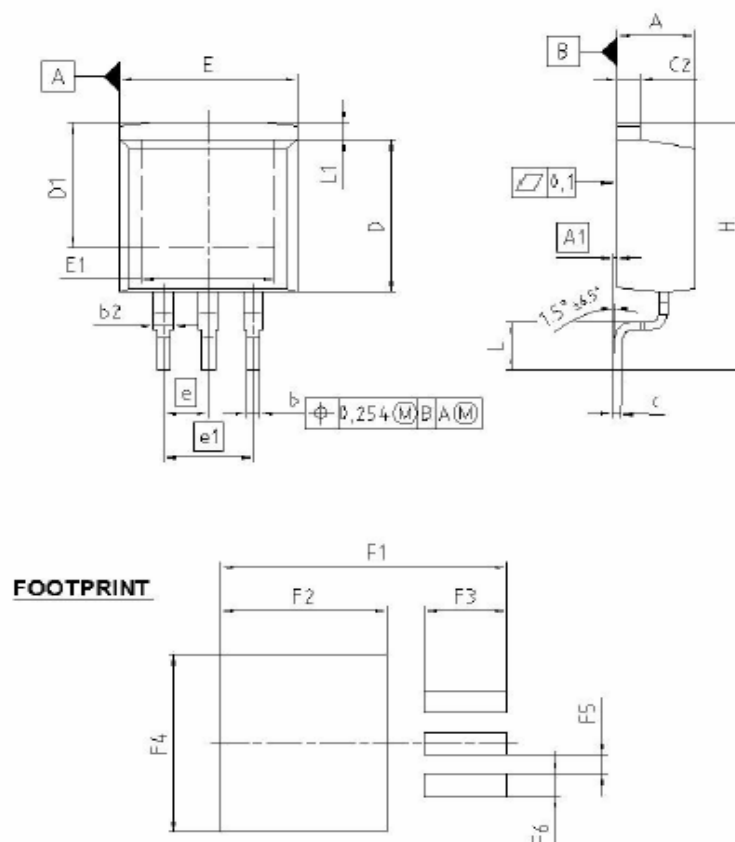
REFERENCE JEDEC TO220
SCALE 0 2.5 5mm
EUROPEAN PROJECTION 
ISSUE DATE 01-06-2005
FILE TO220_1

F
D

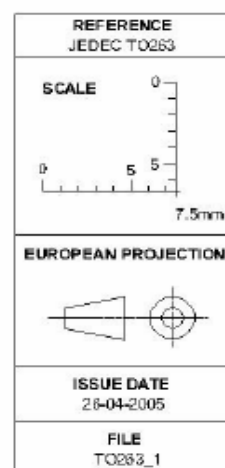
PG-TO262 (I²PAK)


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,300	4,572	0,169	0,180
A1	2,150	2,718	0,085	0,107
b	0,650	0,864	0,026	0,034
b1	0,950	1,093	0,037	0,043
b2	0,950	1,400	0,037	0,055
b3	0,650	1,118	0,026	0,044
c	0,330	0,600	0,013	0,024
c1	1,170	1,400	0,046	0,055
D	8,509	9,450	0,335	0,372
D1	6,900	-	0,272	-
E	9,700	10,363	0,382	0,408
E1	6,500	8,600	0,256	0,339
e	2,540		0,100	
e1	5,080		0,200	
N	3		3	
L	13,000	14,000	0,512	0,551
L1	-	4,800	-	0,189
L2	-	1,727	-	0,068

REFERENCE JEDEC TO262
SCALE 0 2,5 5mm
EUROPEAN PROJECTION 
ISSUE DATE 05-05-2006
FILE TO262_1

P-TO-263-3-2 (D²PAK)


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	0.000	0.254	0.000	0.010
b	0.850	0.850	0.033	0.033
b2	0.950	1.321	0.037	0.052
c	0.330	0.850	0.013	0.033
c2	0.170	1.400	0.006	0.055
D	8.500	9.450	0.335	0.372
D1	7.100	-	0.280	-
E	9.800	10.312	0.386	0.406
E1	6.500	-	0.256	-
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
H	14.605	15.875	0.575	0.625
L	2.200	3.000	0.087	0.118
L1	-	1.800	-	0.071
F1	16.050	16.250	0.632	0.640
F2	9.300	9.500	0.366	0.374
F3	4.500	4.700	0.177	0.185
F4	10.700	10.900	0.421	0.429
F5	1.250	1.450	0.049	0.057
F6	1.100	1.300	0.043	0.051



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